



SUD23N06-31-T4-GE3 Information



For Reference Only

Part Number SUD23N06-31-T4-GE3

Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 21.4A TO252 **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SUD23N06-31-T4-GE3 Specifications

Manufacturer Part Number SUD23N06-31-T4-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 21.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 17nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.7W (Ta), 31.25W (Tc) Rds On (Max) @ Id, Vgs 31 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
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Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 21.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 17nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.7W (Ta), 31.25W (Tc) Rds On (Max) @ Id, Vgs 31 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer	Vishay Siliconix
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C21.4A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs17nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.7W (Ta), 31.25W (Tc)Rds On (Max) @ Id, Vgs31 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	TrenchFET?
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C21.4A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs17nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.7W (Ta), 31.25W (Tc)Rds On (Max) @ Id, Vgs31 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 31 mOhm @ 15A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case 21.4A (Tc) 3V @ 250µA 670PF @ 25V 170C @ 10V 670PF @ 25V 70-25° TO-25° TO-2	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs17nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.7W (Ta), 31.25W (Tc)Rds On (Max) @ Id, Vgs31 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As a signal of the proper distribution of the	Current - Continuous Drain (Id) @ 25°C	21.4A (Tc)
Gate Charge (Qg) (Max) @ Vgs 17nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.7W (Ta), 31.25W (Tc) Rds On (Max) @ Id, Vgs 31 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 31 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max) ± 20 VFET Feature-Power Dissipation (Max) 5.7 W (Ta), 31.25 W (Tc)Rds On (Max) @ Id, Vgs 31 mOhm @ 15 A, 10 VOperating Temperature -55° C $\sim 150^{\circ}$ C (TJ)Mounting TypeSurface MountSupplier Device Package $TO-252$, $(D-Pak)$ Package / Case $TO-252-3$, $DPak$ (2 Leads + Tab), $SC-63$	Gate Charge (Qg) (Max) @ Vgs	17nC @ 10V
FET Feature - Power Dissipation (Max) 5.7W (Ta), 31.25W (Tc) Rds On (Max) @ Id, Vgs 31 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	670pF @ 25V
Power Dissipation (Max) 5.7W (Ta), 31.25W (Tc) Rds On (Max) @ Id, Vgs 31 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs31 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	5.7W (Ta), 31.25W (Tc)
Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	31 mOhm @ 15A, 10V
Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	TO-252, (D-Pak)
	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
Report errors?		Report errors?

SUD23N06-31-T4-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SUD23N06-31-T4-GE3 Payment Methods



















SUD23N06-31-T4-GE3 Shipping Methods













If you have any question about SUD23N06-31-T4-GE3, please do not hesitate to contact us!

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